

MUN2231, MMUN2231L, MUN5231, DTC123EE, DTC123EM3, NSBC123EF3

Digital Transistors (BRT) R1 = 2.2 k Ω , R2 = 2.2 k Ω

NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	12	Vdc
Input Reverse Voltage	V _{IN(rev)}	10	Vdc

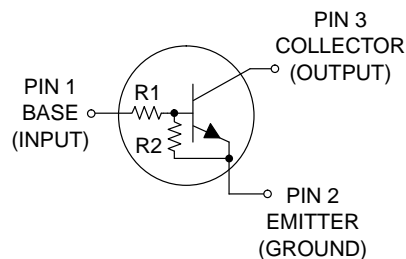
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



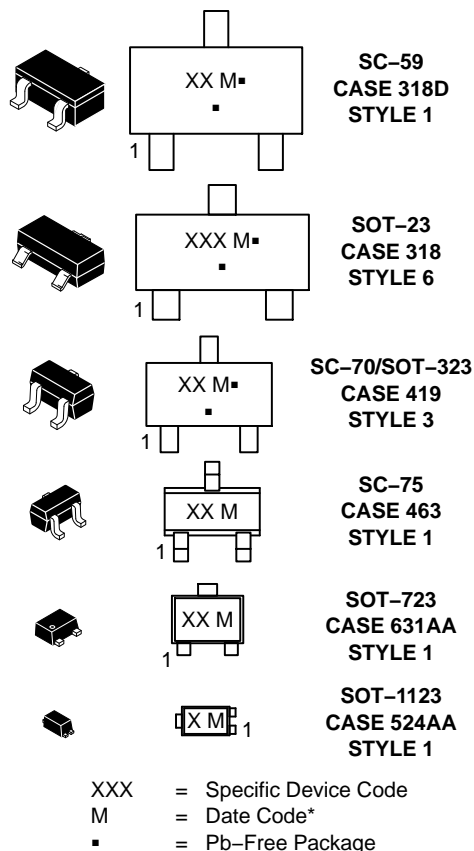
ON Semiconductor®

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PIN CONNECTIONS



MARKING DIAGRAMS



(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

MUN2231, MMUN2231L, MUN5231, DTC123EE, DTC123EM3, NSBC123EF3

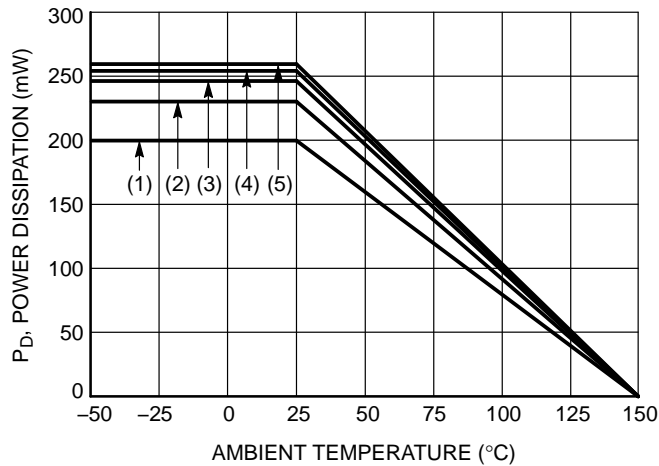
Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping†
MUN2231T1G	8H	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2231LT1G, NSVMMUN2231LT1G*	A8H	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5231T1G	8H	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC123EET1G	8H	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC123EM3T5G, NSVDTC123EM3T5G*	8H	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBC123EF3T5G	E (180°)**	SOT-1123 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

** (xx°) = Degree rotation in the clockwise direction.



- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Figure 1. Derating Curve

MUN2231, MMUN2231L, MUN5231, DTC123EE, DTC123EM3, NSBC123EF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC–59) (MUN2231)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1) (Note 2) (Note 1) (Note 2)	230 338 1.8 2.7	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (Note 1) (Note 2)	540 370	°C/W
Thermal Resistance, Junction to Lead	$R_{\theta JL}$ (Note 1) (Note 2)	264 287	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C
THERMAL CHARACTERISTICS (SOT–23) (MMUN2231L)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1) (Note 2) (Note 1) (Note 2)	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (Note 1) (Note 2)	508 311	°C/W
Thermal Resistance, Junction to Lead	$R_{\theta JL}$ (Note 1) (Note 2)	174 208	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C
THERMAL CHARACTERISTICS (SC–70/SOT–323) (MUN5231)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1) (Note 2) (Note 1) (Note 2)	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (Note 1) (Note 2)	618 403	°C/W
Thermal Resistance, Junction to Lead	$R_{\theta JL}$ (Note 1) (Note 2)	280 332	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C
THERMAL CHARACTERISTICS (SC–75) (DTC123EE)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1) (Note 2) (Note 1) (Note 2)	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (Note 1) (Note 2)	600 400	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C
THERMAL CHARACTERISTICS (SOT–723) (DTC123EM3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1) (Note 2) (Note 1) (Note 2)	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (Note 1) (Note 2)	480 205	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C

1. FR–4 @ Minimum Pad.
2. FR–4 @ 1.0 x 1.0 Inch Pad.
3. FR–4 @ 100 mm², 1 oz. copper traces, still air.
4. FR–4 @ 500 mm², 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBC123EF3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 3) (Note 4) (Note 3) (Note 4)	 254 297 2.0 2.4	 mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (Note 3) (Note 4)	493 421	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$ (Note 3)	193	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm², 1 oz. copper traces, still air.
4. FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$)	I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$)	I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$)	I_{EBO}	–	–	2.3	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 5) ($I_C = 2.0\text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	–	–	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) ($I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$)	h_{FE}	8.0	15	–	
Collector-Emitter Saturation Voltage (Note 5) ($I_C = 10\text{ mA}, I_B = 5.0\text{ mA}$)	$V_{CE(sat)}$	–	–	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0\text{ V}, I_C = 100\text{ }\mu\text{A}$)	$V_{i(off)}$	–	1.2	0.5	Vdc
Input Voltage (on) ($V_{CE} = 0.3\text{ V}, I_C = 20\text{ mA}$)	$V_{i(on)}$	2.0	1.7	–	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.25\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	–	–	Vdc
Input Resistor	R_1	1.5	2.2	2.9	k Ω
Resistor Ratio	R_1/R_2	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS
MUN2231, MMUN2231L, MUN5231, DTC123EE, DTC123EM3

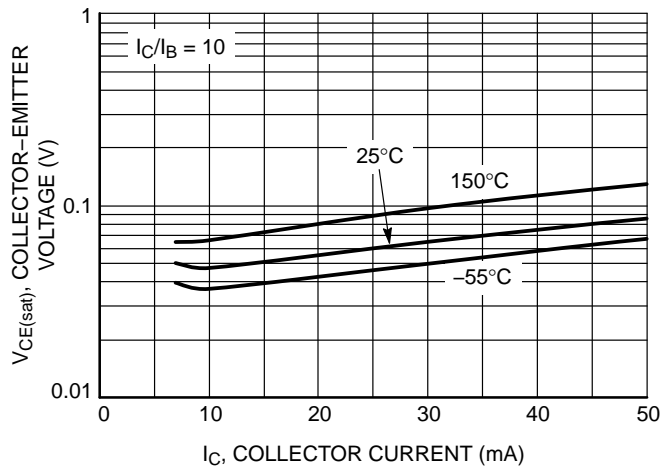


Figure 2. $V_{CE(sat)}$ vs. I_C

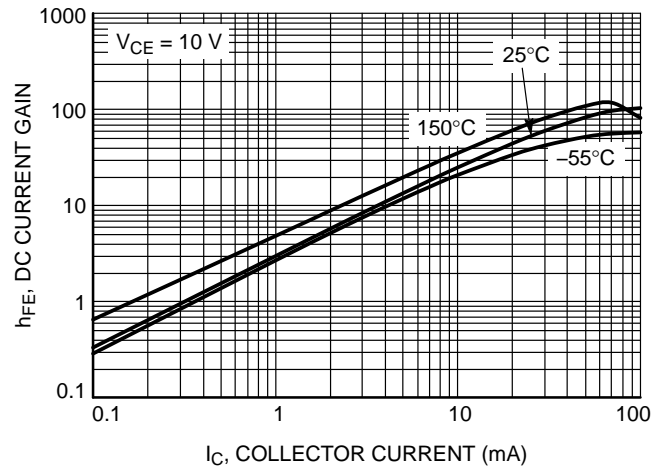


Figure 3. DC Current Gain

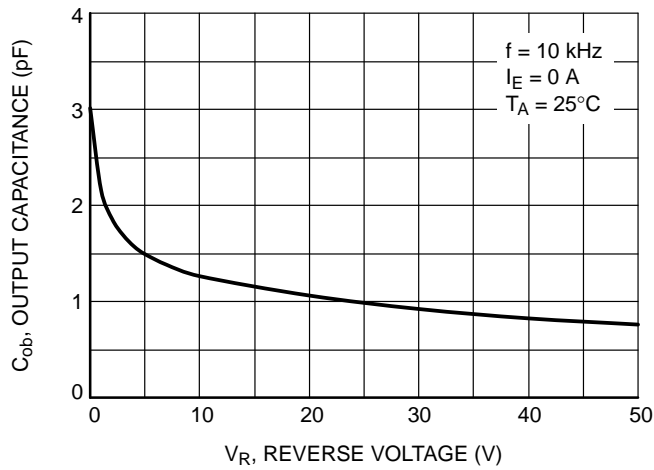


Figure 4. Output Capacitance

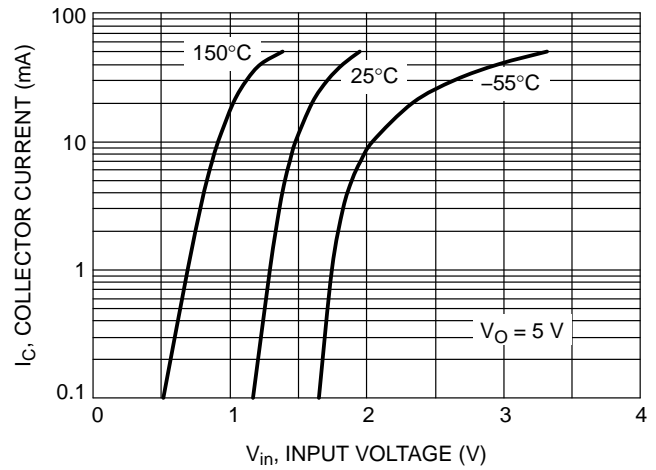


Figure 5. Output Current vs. Input Voltage

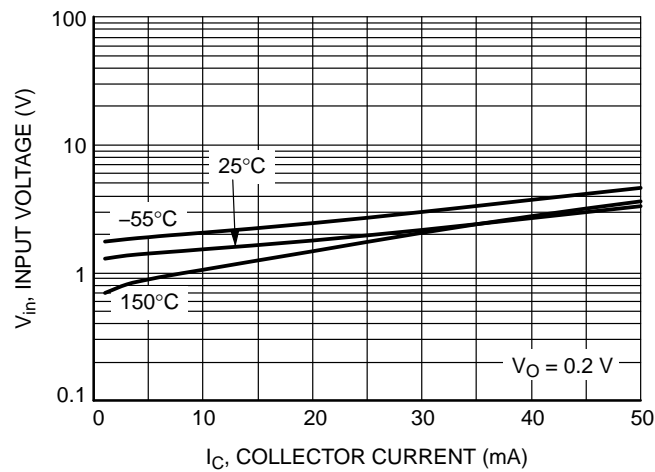
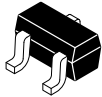


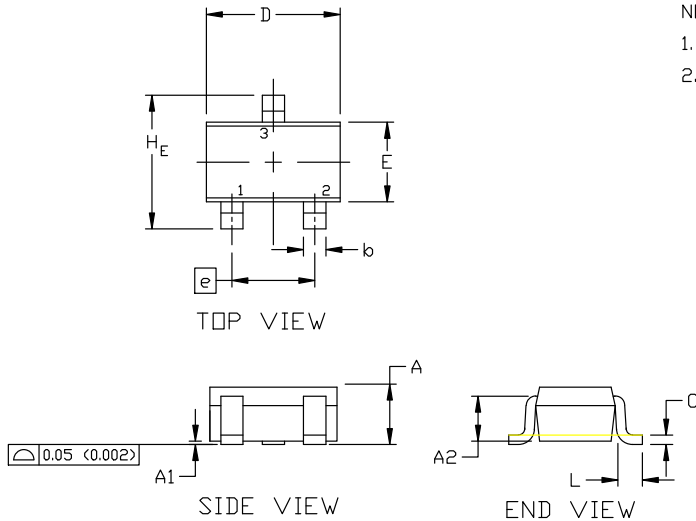
Figure 6. Input Voltage vs. Output Current



SCALE 4:1

SC-70 (SOT-323)
CASE 419
ISSUE R

DATE 11 OCT 2022

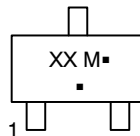


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

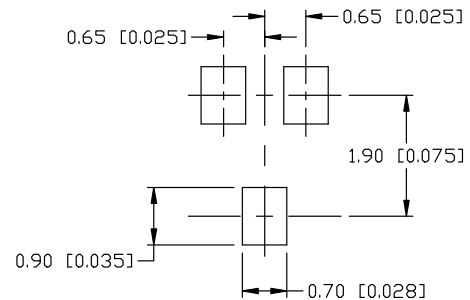
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC
MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE

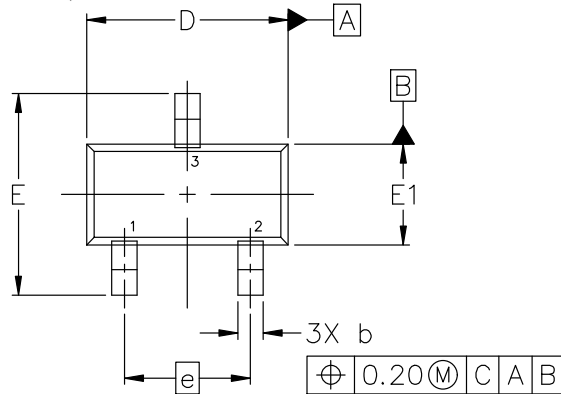
STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

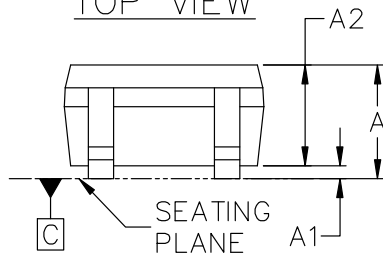
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SC75-3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

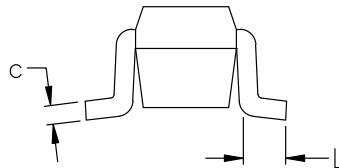
DATE 01 FEB 2024



TOP VIEW

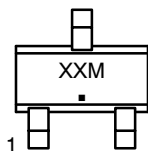


SIDE VIEW



END VIEW

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

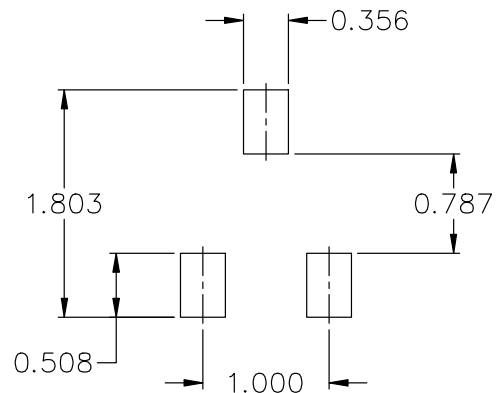
STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2	0.80 REF.		
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e	1.00 BSC		
L	0.10	0.15	0.20

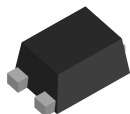


RECOMMENDED MOUNTING FOOTPRINT*

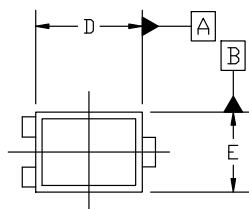
* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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DESCRIPTION:	SC75-3 1.60x0.80x0.80, 1.00P	PAGE 1 OF 1

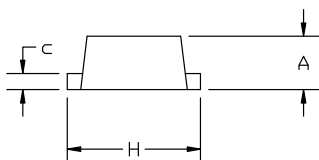
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SOT-1123 0.80x0.60x0.37, 0.35P
CASE 524AA
ISSUE D

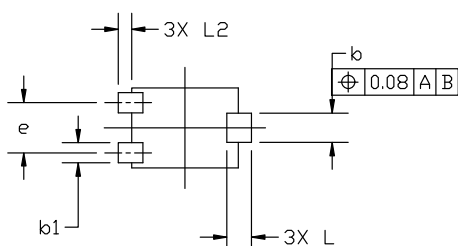
DATE 18 JAN 2024



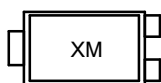
TOP VIEW



SIDE VIEW



BOTTOM VIEW

GENERIC
MARKING DIAGRAM*

X = Specific Device Code
M = Date Code

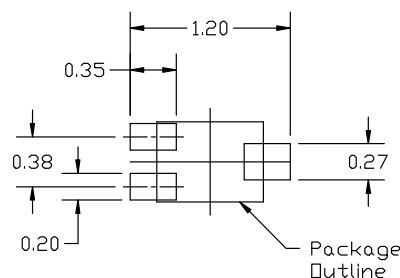
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS

DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.15	0.22	0.28
b1	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
e	0.35	0.38	0.40
H	0.950	1.000	1.050
L	0.185 REF		
L2	0.05	0.10	0.15


RECOMMENDED
MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERM/D.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

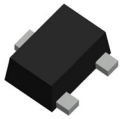
DOCUMENT NUMBER: 98AON23134D

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DESCRIPTION: SOT-1123 0.80x0.60x0.37, 0.35P

PAGE 1 OF 1

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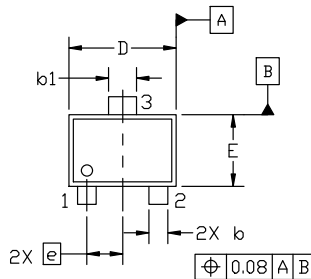


SOT-723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

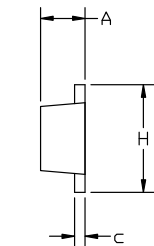
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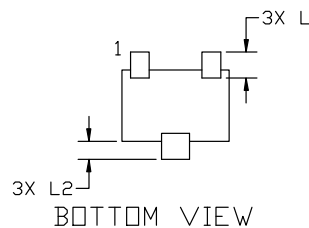
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
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4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



TOP VIEW

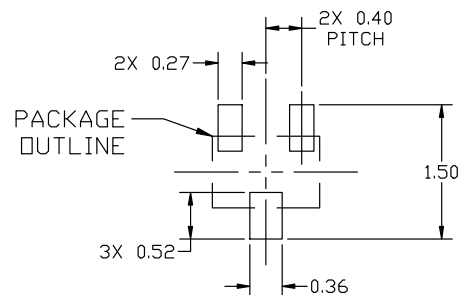


SIDE VIEW



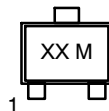
BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



RECOMMENDED MOUNTING
FOOTPRINT

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
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DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P	PAGE 1 OF 1

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